



Bipolar NPN Bare Die – BTN481

Part Description

The BTN481 is a silicon BJT transistor available in bare die form and well suited for use in High Speed Switching applications.

Key Parameters:

- VCBO = 40V
- VCEO = 15V
- VEBO = 4.5V
- hFE = 120- @ VCE = 1V, IC = 0.01A
- VCE(Sat) = 0.5V @ IC = 0.1A, IB = 10mA
- fT = - MHz @ VCE = - V, IE = - A
- COBO = 4pF @ VCB = 5V

Features

Designed as a direct replacement for FAIRCHILD / ON SEMI MMBT2369, MMBT2369A, 2N2369, 2N2369A

Die Size (Unawn)

360 μ m X 220 μ m, 14 Mils X 9 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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